

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π-MOSV)

2SK2545

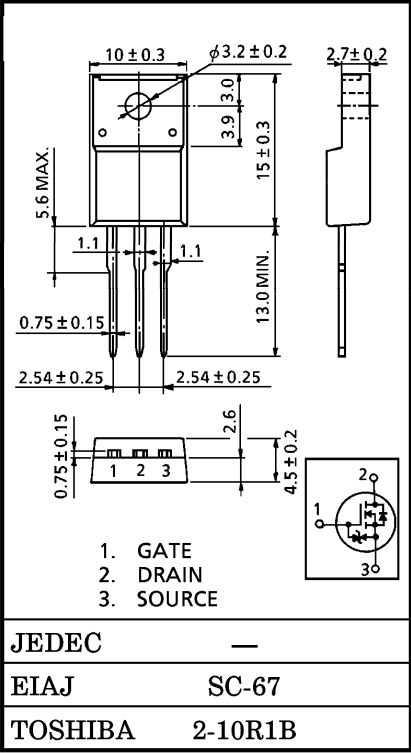
HIGH SPEED, HIGH VOLTAGE SWITCHING APPLICATIONS
DC-DC CONVERTER, RELAY DRIVE AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS
Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)}=0.9\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}|=5.5S$ (Typ.)
- Low Leakage Current : $I_{DSS}=100\mu A$ (Max.) ($V_{DS}=600V$)
- Enhancement-Mode : $V_{th}=2.0\sim 4.0V$ ($V_{DS}=10V$, $I_D=1mA$)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Drain-Gate Voltage ($R_{GS}=20k\Omega$)		V_{DGR}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	DC	I_D	6	A
	Pulse	I_{DP}	24	A
Drain Power Dissipation ($T_c=25^\circ C$)		P_D	40	W
Single Pulse Avalanche Energy**		E_{AS}	345	mJ
Avalanche Current		I_{AR}	6	A
Repetitive Avalanche Energy*		E_{AR}	4	mJ
Channel Temperature		T_{ch}	150	°C
Storage Temperature Range		T_{stg}	$-55\sim 150$	°C



Weight : 1.9g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	3.125	°C / W
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	62.5	°C / W

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

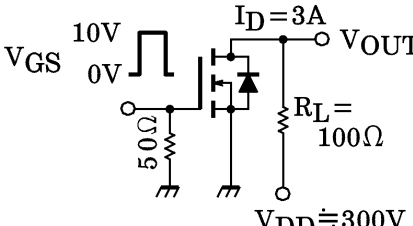
** $V_{DD}=90V$, $T_{ch}=25^\circ C$ (initial), $L=16.8mH$, $R_G=25\Omega$, $I_{AR}=6A$

This transistor is an electrostatic sensitive device.
Please handle with caution.

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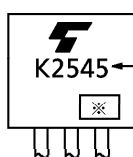
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 25V, V_{DS} = 0V$	—	—	± 10	μA
Gate-Source Breakdown Voltage		$V_{(BR)GSS}$	$I_G = \pm 10\mu A, V_{DS} = 0V$	± 30	—	—	V
Drain Cut-off Current		I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V$	—	—	100	μA
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = 10mA, V_{GS} = 0V$	600	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10V, I_D = 1mA$	2.0	—	4.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 3A$	—	0.9	1.25	Ω
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10V, I_D = 3A$	2.0	5.5	—	S
Input Capacitance		C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$	—	1300	—	pF
Reverse Transfer Capacitance		C_{rss}		—	130	—	
Output Capacitance		C_{oss}		—	400	—	
Switching Time	Rise Time	t_r	 $V_{IN} : t_r, t_f < 5ns,$ $Duty \leq 1\%, t_W = 10\mu s$	—	25	—	ns
	Turn-on Time	t_{on}		—	45	—	
	Fall Time	t_f		—	40	—	
	Turn-off Time	t_{off}		—	150	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} \approx 400V, V_{GS} = 10V, I_D = 6A$	—	30	—	nC
Gate-Source Charge		Q_{gs}		—	18	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	12	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	6	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	24	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 6A, V_{GS} = 0V$	—	—	-1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 6A, V_{GS} = 0V$	—	1000	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR} / dt = 100A / \mu s$	—	7.0	—	μC

MARKING



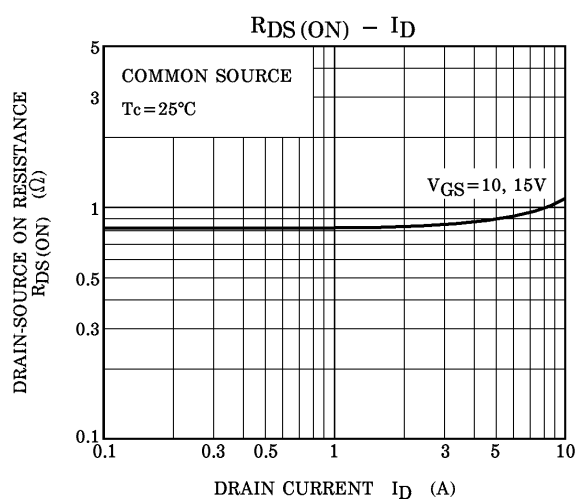
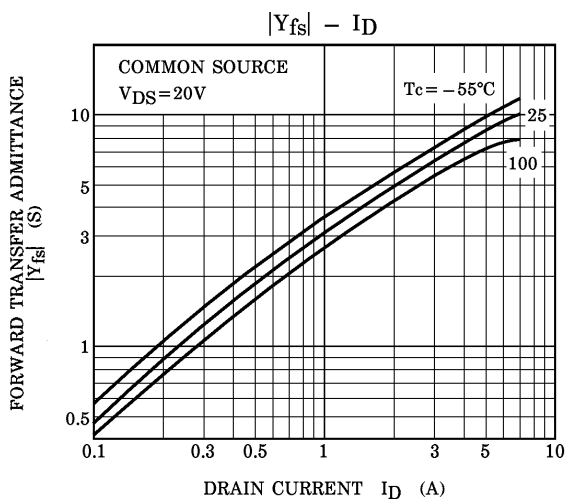
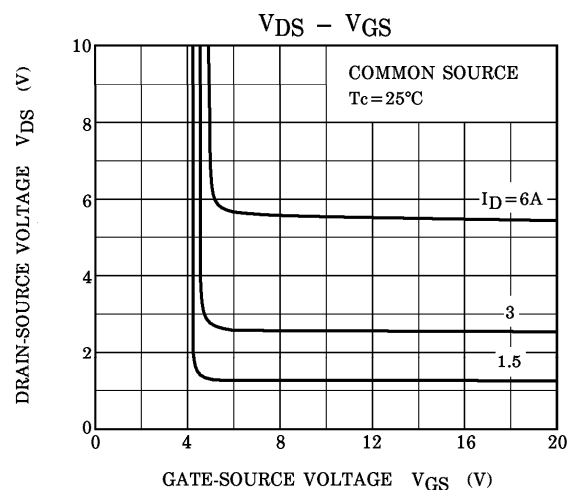
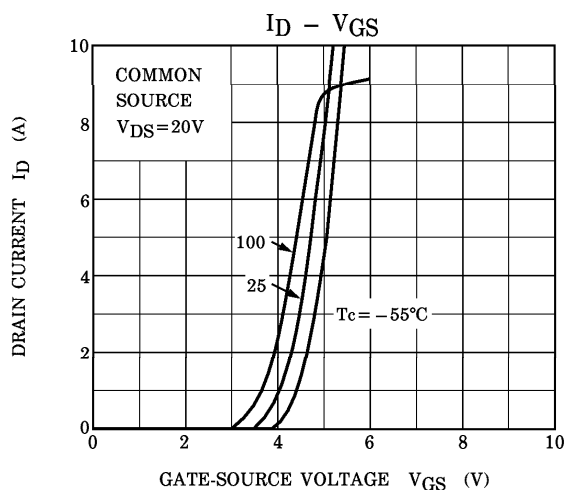
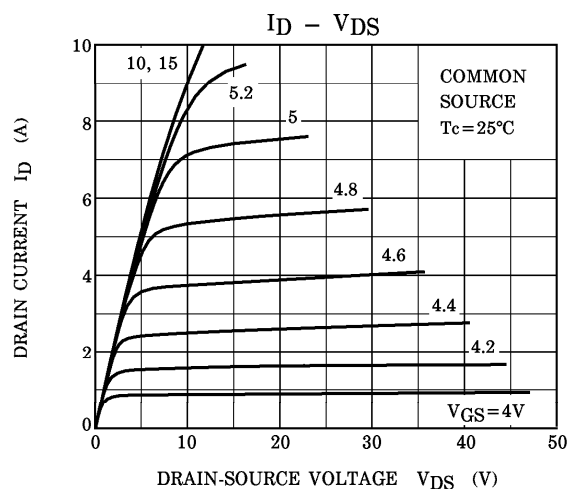
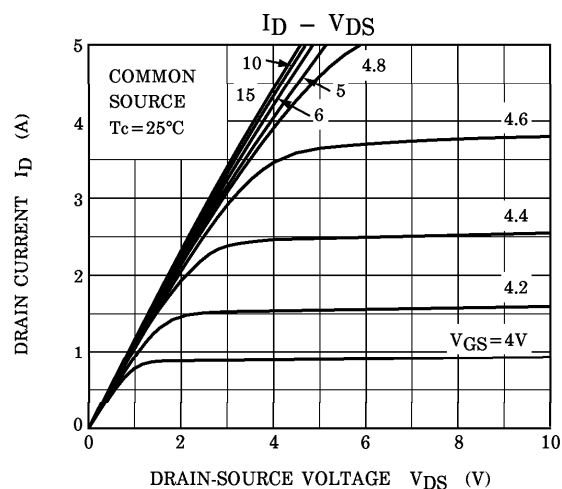
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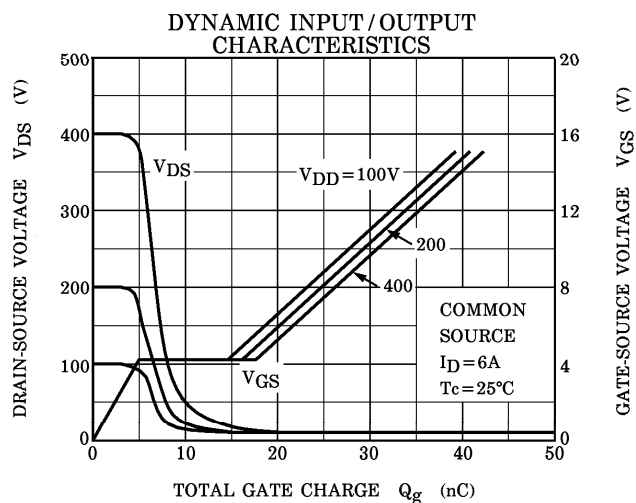
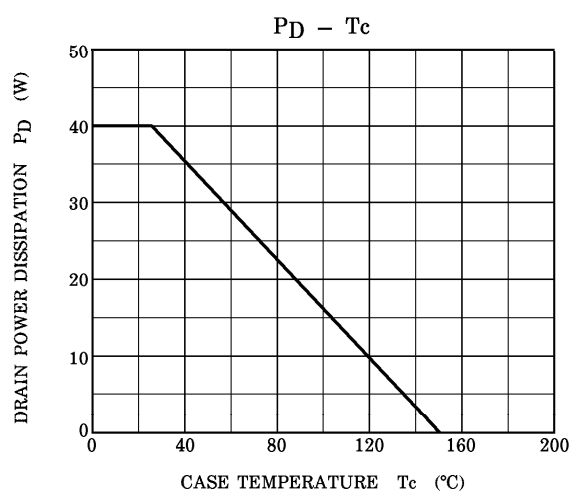
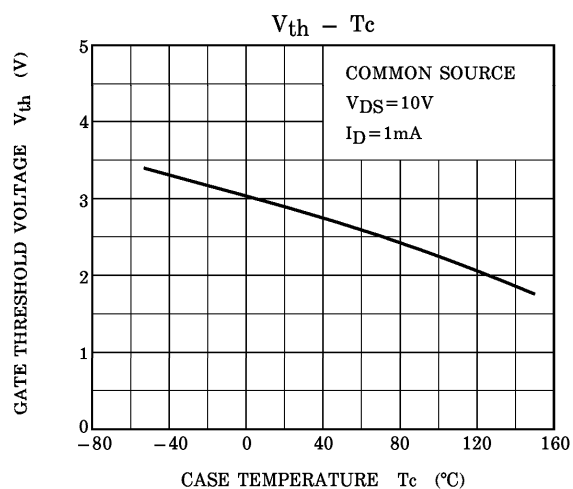
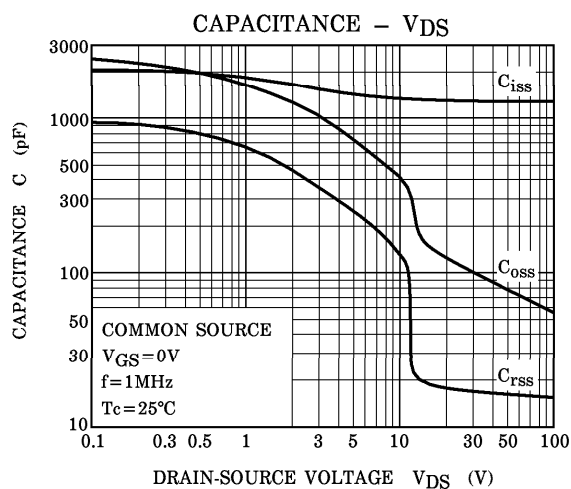
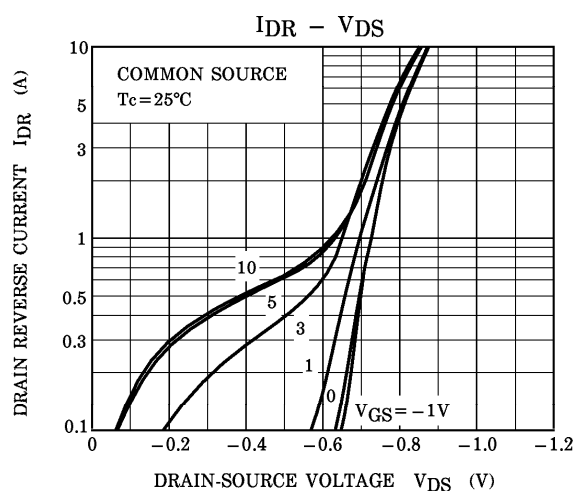
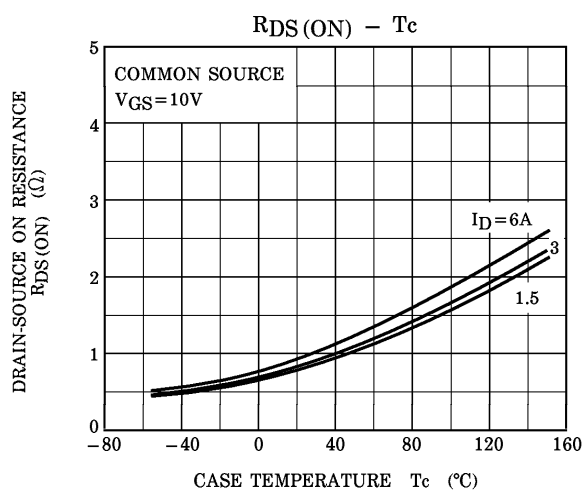
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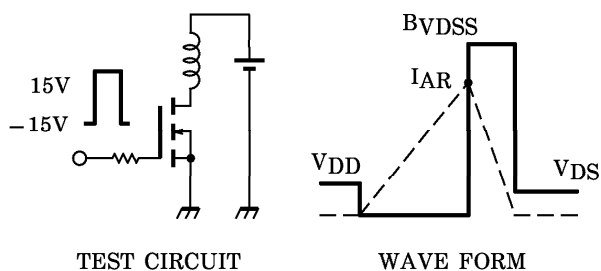
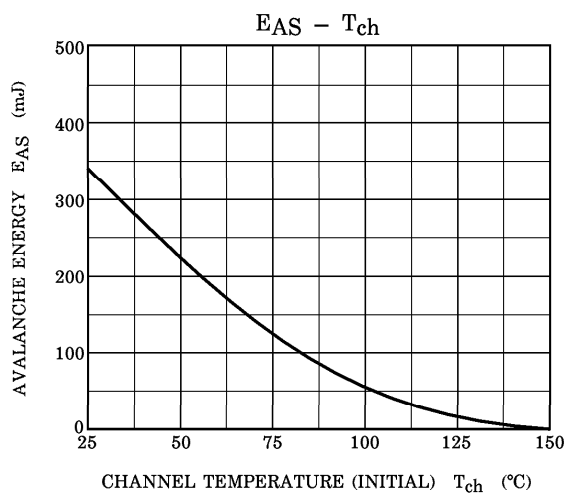
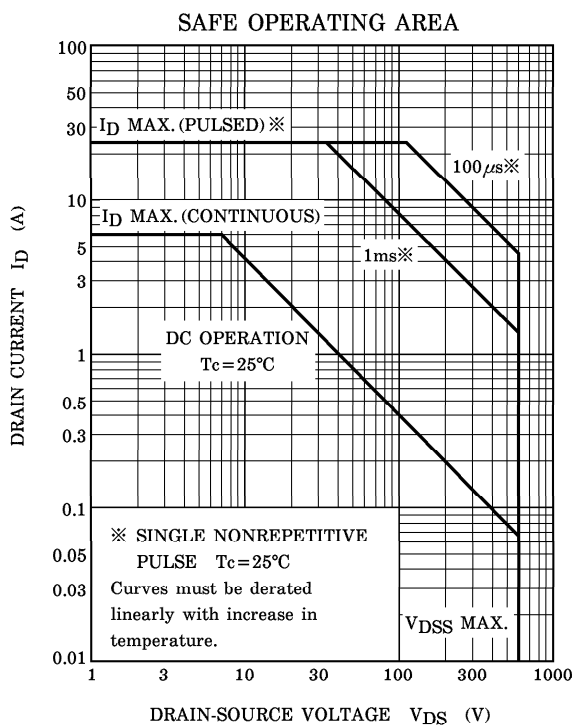
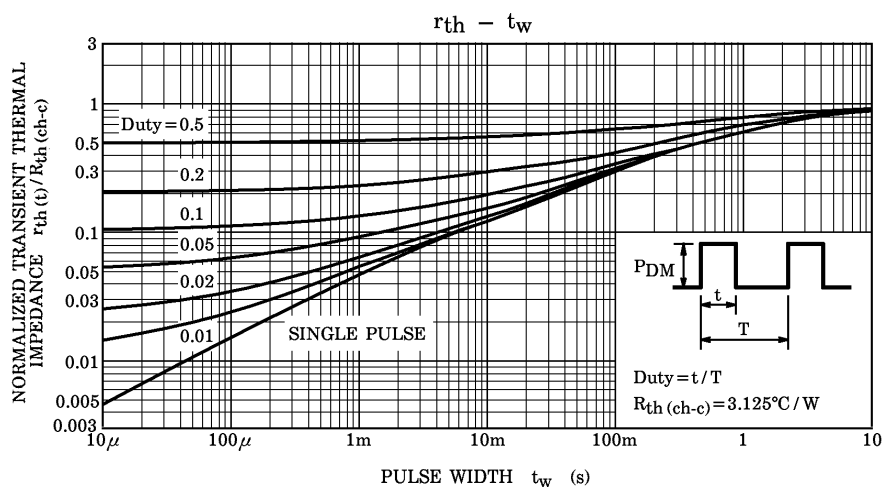


Month (Starting from Alphabet A)

Year (Last Number of the Christian Era)







Peak $I_{AR} = 6A$, $R_G = 25\Omega$
 $V_{DD} = 90V$, $L = 16.8mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$